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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: January 14, 2004 (use as many sheets as necessary)				Complete if Known	
				Application Number	10/757/177
				Filing Date	
				First Named Inventor	J. Scott Price
				Group Art Unit	
				Examiner Name	
				Attorney Docket Number	070191-0362 (112019)
Sheet	1	of	2		

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
HKS	A1	6,333,968	B1	Whitlock et al.	12/25/2001	
	A2	6,297,592	B1	Goren et al.	10/02/2001	
	A3	5,844,216		Fathi et al.	12/01/1998	
	A4	4,289,969		Cooperstein et al.	09/15/1981	
	A5	4,012,656		Norman et al.	03/15/1977	

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ⁵ (if known)				

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), -volume-issue number(s), publisher, city and/or country where published.	T ⁶
HKS	A6	"Soft lithography used to fabricate transistors on curved substrates"; 3-pg. document; [obtained from Internet www.news.uiuc.edu/scitips/00/11softlitho.html]; [printed on 10/26/01].	
	A7	"Soft Lithography"; 5-pg. document; published January 1998; WTECHyper-Librarian.	
	A8	"The future of electronics manufacturing is revealed in the fine print"; Ralph G. Nuzzo; PNAS; Vol. 98, No. 9, pp. 4827-4829 (April 24, 2001).	
	A9	"Low-Temperature Fabrication of Si Thin-Film Transistor Microstructures by Soft Lithographic Patterning on Curved and Planar Substrates"; Erhardt et al.; Chemistry of Materials, Vol. 12, No. 11, pp. 3306-3315 (11/2000).	
HKS	A10	"Nucleation and growth of carbon nanotubes by microwave plasma chemical vapor deposition"; Bower et al.; Applied Physics Letters, Vol. 77, No. 17, pp. 2767-2769 (10/23/00).	

Examiner Signature	Hoon Sony	Date Considered	2/15/04
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HPS	A11	"Large current density from carbon nanotube field emitters"; Zhu et al.; Applied Physics Letters, Vol. 75, No. 6, pp. 873-875 (8/9/99).	
	A12	"Application of carbon nanotubes as electrodes in gas discharge tubes"; Rosen et al.; Applied Physics Letters, Vol. 76, No. 13, pp. 1668-1670 (3/27/00).	
	A13	"Work functions and valence band states of pristine and Cs-intercalated single-walled carbon nanotube bundles"; Applied Physics Letters, Vol. 76, No. 26, pp. 4007-4009 (6/26/00).	
	A14	"Fabrication and Field Emission Properties of Carbon Nanotube Cathodes"; Bower et al.; 6-pg. document; Proceeding of 1999 MRS Fall Meeting.	
	A15	"10 Applications of Carbon Nanotubes"; Ajayan et al.; pp. 274-315.	
	A16	"Patterned negative electron affinity photocathodes for maskless electron beam lithography"; Schneider et al.; J. Vac. Sci. Technol.; pp. 3192-3196 (Nov/Dec 1998).	
	A17	"Semiconductor on glass photocathodes for high throughput maskless electron beam lithography"; Baum et al.; J. Vac. Sci. Technol.; pp. 2707-2712 (Nov/Dec 1998).	
HPS	A18	"Physical properties of thin-film field emission cathodes with molybdenum cones"; Spindt et al.; Journal of Applied Physics, Vol. 47, No. 12, pp. 5248-5263 (December 1976).	
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Examiner Signature	Heon Soy	Date Considered	2/15/04
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